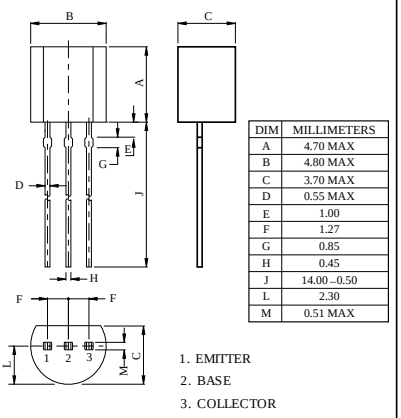
2N6517 TRANSISTOR (NPN)



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.55 MAX
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00 –0.50
L	2.30
M	0.51 MAX

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FEATURES

- Complement To 2N6520

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	350	V
V_{CEO}	Collector-Emitter Voltage	350	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	0.5	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=0.1mA,I_E=0	350			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	350			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.01mA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=250V,I_E=0			0.05	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.05	μA
DC current gain	h_{FE}*	V_{CE}=10V, I_C=1mA	20			
		V_{CE}=10V, I_C=10mA	30			
		V_{CE}=10V, I_C=30mA	30		200	
		V_{CE}=10V, I_C=50mA	20		200	
		V_{CE}=10V, I_C=100mA	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=10mA,I_B=1mA			0.3	V
		I_C=50mA,I_B=5mA			1	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$*	I_C=10mA,I_B=1mA			0.75	V
		I_C=20mA,I_B=2mA			0.85	V
		I_C=30mA,I_B=3mA			0.9	V
Base-emitter voltage	V_{BE}*	V_{CE}=10V, I_C=100mA			2	V
Transition frequency	f_T*	V_{CE}=20V,I_C=10mA,f=20MHz	40		200	MHz
Collector output capacitance	C_{ob}	V_{CB}=20V,I_E=0, f=1MHz			6	pF

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.